

<b>Form PTO-1449 (Modified)</b>				<b>Atty Docket N .:</b> 003692.P007XD3		<b>S rial No.:</b>  <b>Not Yet Assign d</b>	
List of Patents and Publications Statement  (Use several sheets if necessary)				<b>Applicants:</b> Rumennik, V., et al.			
				<b>Filing Date:</b> September 20, 2001 (Concurrently Herewith)			

11000 U.S. PTO  
09/961229  
09/20/01

REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
Exam. Initial	Date	Document Number	Name	Class	Sub-Class	Filing Dat	
SK	10/21/86	4,618,541	Forouhi, et al.				
	12/02/86	4,626,879	Colak				
	05/12/87	4,665,426	Allen, et al.				
	06/28/88	4,754,310	Coe				
	08/16/88	4,764,800	Sander				
	03/07/89	4,811,075	Elkund				
	12/26/89	4,890,146	Williams, et al.				
	05/01/90	4,922,327	Mena, et al.				
	04/23/91	5,010,024	Allen, et al.				
	06/18/91	5,025,296	Fullerton, et al.				
✓	09/08/92	5,146,298	Elkund				

FOREIGN PATENT DOCUMENTS							
N .	Document No.	Date	Country	Name	Class	Sub-Class	Trans-lation
SK	DE 43 09 764	09/29/94	Germany				
↓	57-12557	1/22/82	Japan				
↓	56-38867	4/14/81	Japan				

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
SK	Appels and Vaes, "High Voltage Thin Layer Devices (RESURF Devices)," IEDM Tech. Digest, pp. 238-241, 1979.
↓	Fujihira ("Theory of Semiconductor Superjunction Devices," Jpn. J. Appl. Phys., Vol. 36, pp. 6254-6262, Oct. 1997)
↓	Patent Abstract of Japan, Vol. 018, No. 590 (E-1628), 11/10/94 and JP 06224426 (Matsushita Electron Corp.) 08/12/94

<b>Examiner</b>  <i>Shourang</i>	<b>Date Considered</b>  <i>4/14/03</i>
--	--

**EXAMINER:** Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<b>Form PTO-1449 (Modified)</b>				<b>Atty Docket No.:</b> 003692.P007XD3		<b>S rial No.:</b> <b>N t Yet Assigned</b>	
List of Patents and Publications Statement (Use several sheets if necessary)				<b>Applicants:</b> Rumennik, V., et al.			
				<b>Filing Date:</b> September 20, 2001 (Concurrently Herewith)			

  

REFERENCE DESIGNATION				U.S. PATENT DOCUMENTS			
Exam. Initial	Date	Document Number	Name	Class	Sub-Class	Filing Date	
<i>See</i>	10/13/92	5,155,574	Yamaguchi				
	08/17/93	5,237,193	Williams, et al.				
	11/02/93	5,258,636	Rumennik, et al.				
	12/14/93	5,270,264	Andideh, et al.				
	05/17/94	5,313,082	Eklund				
	06/28/94	5,324,683	Fitch, et al.				
	09/20/94	5,349,225	Redwine, et al.				
	10/25/94	5,359,221	Miyamoto, et al.				
	01/31/95	5,386,136	Williams, et al.				
	08/01/95	5,438,215	Tihanyi				
<i>✓</i>	05/28/96	5,521,105	Hsu, et al.				

  

FOREIGN PATENT DOCUMENTS							
N .	Document No.	Date	Country	Name	Class	Sub-Class	Trans-lation
<i>d</i> <i>See</i>	57-12558	1/22/82	Japan				
<i>s</i> <i>See</i>	6-224426	12/8/94	Japan	Yuji			
<i>b</i> <i>See</i> <i>✓</i>	JP04107877A	04/09/92	Japan	Yamanishi, Y. et al.			

  

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
<i>See</i>	Patent Abstract of Japan, Vol. 016, No. 347 (E-1240), 07/27/92 and JP 04 107867 (Matsushita Electron Corp.) 04/09/92
<i>*</i>	<del>Air-Gap Formation During IMD Deposition to Lower Interconnect Capacitance, B. Shieh, K.C. Saraswat, IEEE Electron Device Letters, Vol., 19, No. 1, January 1998</del>
<i>*</i>	<del>Modeling and Optimization of Lateral High Voltage IC Devices To Minimize 3-D Effects, Hamza Yilmaz, R&amp;D Engineering, Semiconductor Business Division, General Electric Company, NC., pages 290 - 294</del>

  

<b>Examiner</b> <i>Shousang Hu</i>	<b>Date Considered</b> <i>4/14/03</i>
---------------------------------------	--

  

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*\*: Note, these two references are not found.*

<b>Form PTO-1449 (Modified)</b>				<b>Atty Dock t No.:</b> 003692.P007XD3		<b>S rial No.:</b> Not Y t Assign d	
List of Patents and Publications Statement  (Use several sheets if necessary)				<b>Applicants:</b> Rumennik, V., et al. <b>Filing Date:</b> September 20, 2001 (Concurrently Herewith)			
<b>REFERENCE DESIGNATION</b>				<b>U.S. PATENT DOCUMENTS</b>			
<b>Exam. Initial</b>		<b>Date</b>	<b>Document Number</b>	<b>Name</b>	<b>Class</b>	<b>Sub-Class</b>	<b>Filing Dat</b>
SR		08/27/96	5,550,405	Cheung, et al.			
SR		08/05/97	5,654,206	Merrill			
SR		08/12/97	5,656,543	Chung			
SR		08/19/97	5,659,201	Wollesen			
		<del>08/27/96</del>	<del>5,550,405</del>	<del>Cheung, et al.</del>			
		<del>08/05/97</del>	<del>5,654,206</del>	<del>Merrill</del>			
		<del>08/12/97</del>	<del>5,656,543</del>	<del>Chung</del>			
		<del>08/19/97</del>	<del>5,659,201</del>	<del>Wollesen</del>			
SR		08/24/99	5,943,595	Akiyama, et al.			
SR		01/04/00	6,010,926	Rho, et al.			
<b>FOREIGN PATENT DOCUMENTS</b>							
<b>No.</b>		<b>Document No.</b>	<b>Date</b>	<b>Country</b>	<b>Name</b>	<b>Class</b>	<b>Sub-Class</b>
<b>OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)</b>							
<b>Examin r</b> <i>Shoung Lee</i>				<b>Date Considered</b> <i>4/14/03</i>			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							